



1449A/PTO Rev. 10/95		U.S. Department of Commerce Patent and Trademark Office		Compleat If Known	
LIST OF PRIOR ART CITED BY APPLICANT (use as many sheets as necessary)				Application Number	10-677,005
				Filing Date	September 30, 2003
				First Named Inventor	Jer-shen Maa
				Group Art Unit	1763
				Examiner Name	Goudreau
Sheet	1	of	1	Attorney Docket No.	SLA.0780

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, country where published, source.	T ²
gag		K. RIM <i>et al.</i> , <i>Strained Si for sub-100 nm MOSFETs</i> , Proceedings of the 3rd International Conference on SiGe Epitaxy and Heterostructures, Sante Fe, New Mexico, March 9-12, 2002, p125.	
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		Z.-Y. CHENG <i>et al.</i> , <i>SiGe-on insulator (SGOI): Substrate Preparation and MOSFET Fabrication for Electron Mobility Evaluation</i> , 2001 IEEE International SOI Conference Proceedings p 13.	
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Examiner Signature	George Goudreau	Date Considered	10-051
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Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Unique citation designation number. ²Applicant is to place a check mark here if English language Translation is attached.